The oxidation/diffusion clean for silicon wafers consist of three chemical baths. SC1 for residual organics, SC2 for metal impurities and HF dip to remove any native oxide.

**SC1 bath**

mixture 5:1:0.5 H2O:H2O2:NH4OH

time=10min; temp=70C

**SC2 bath**

mixture 6:1:1 H2O:H2O2:HCL

time=15min; temp=70C

**Procedure**

1) SC1 bath
2) DI water rinse
3) brief soak in 50:1 H2O:HF (HF dip) at RT for ~15 seconds
4) brief DI water rinse
5) SC2 bath
6) DI water rinse
7) SRD rinse/dry